

FOR USE BY ELECTRICIANS OVERSEAS:

最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型 名	社 名	用 途	構 造	最大 定 格 ($T_a=25^{\circ}\text{C}$)					電 気 的 特 性 ($T_a=25^{\circ}\text{C}$)										外 形	備 考
				V_{CBO} (V)	V_{CEO} (V)	I_C (mA)	P_C (mW)	T_j ($^{\circ}\text{C}$)	I_{CBO} 最大値 (μA)	$V_{CE(V)}$	直流又はパルス h_{FE} I_C (mA)	バイアス $V_{CE(V)}$	h_{FE} h_{FE}^*	h_{ie} h_{ie}^* (Ω)	h_{re} h_{re}^* ($\times 10^{-4}$)	h_{oe} h_{oe}^* (μS)	$f_{\alpha b}$ $f_{\alpha b}^*$ (Mc)	C_{ob} (pF)		
1	2	3	4	5					6	7	8					9	10	11	12	

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{cso} MAXIMUM VALUE AND V_{ce} VALUE (CRITERIA FOR MEASURING I_{cso})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{ce} , I_c (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{ce} , I_c (CRITERIA FOR MEASURING h PARAMETERS)

* INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.

- 9 $f_{\alpha b}$ OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_T .
- 10 C_{ob} AND $r_{bb'}$ OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN $r_{bb'}$ COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
- 11 OUTLINE
- 12 REMARKS

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